

Yoshiyuki Yamashita

List of Publications by Year in descending order

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185
papers

4,045
citations

109321

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149698

56
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189
all docs

189
docs citations

189
times ranked

5086
citing authors

#	ARTICLE	IF	CITATIONS
1	Experimental and theoretical studies on atomic structures of the interface states at SiO ₂ /4H-SiC(0001) interface. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	3
2	Chemical States of Active and Inactive Dopant Sites in Si-doped GaN(0001). <i>Vacuum and Surface Science</i> , 2022, 65, 309-314.	0.1	0
3	Purpose of this Special Issue: "Vacuum and Surface Science of Films". <i>Vacuum and Surface Science</i> , 2021, 64, 154-155.	0.1	0
4	Atomic Structures and Interface States Density at SiO ₂ /4H-SiC Interface. <i>Vacuum and Surface Science</i> , 2021, 64, 312-317.	0.1	0
5	Atomic Structures and Chemical States of Active and Inactive Dopant Sites in Si-Doped GaN. <i>ACS Applied Electronic Materials</i> , 2021, 3, 4618-4622.	4.3	4
6	Unraveling the Resistive Switching Mechanisms in LaMnO ₃ -Based Memristive Devices by Operando Hard X-ray Photoemission Measurements. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5555-5562.	4.3	5
7	Purpose of the Special Issue: "Recent progress in Practical Surface Analysis". <i>Vacuum and Surface Science</i> , 2021, 64, 492-492.	0.1	0
8	Origin of Fermi level pinning in high- <i>k</i> gate stack structures studied by operando hard x-ray photoelectron spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2020, 238, 146890.	1.7	1
9	Photoelectron spectroscopic study on electronic state of corundum In ₂ O ₃ epitaxial thin film grown by mist-CVD. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIIG12.	1.5	4
10	Band alignment at non-polar AlN/MnS interface investigated by hard X-ray photoelectron spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIIG07.	1.5	2
11	Interface chemistry of pristine TiN/La:Hf _{0.5} Zr _{0.5} O ₂ capacitors. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	35
12	Evaluation of Band Alignment of SrNbO ₂ N Using Hard X-ray Photoelectron Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2020, 124, 5528-5532.	3.1	5
13	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In ₂ O ₃ (111) single crystal. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SDDG06.	1.5	7
14	Photoelectron spectroscopic study on electronic state and electrical properties of SnO ₂ single crystals. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 080903.	1.5	6
15	Reaction mechanism of ZrO _x metal resists with extreme ultraviolet irradiation. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SDDC01.	1.5	4
16	Relationship between band-offset, gate leakage current, and interface states density at SiO ₂ /4H-SiC (000-1) interface. <i>AIP Advances</i> , 2019, 9, 045002.	1.3	4
17	Spectroscopic Observation of the Interface States at the SiO ₂ /4H-SiC(0001) Interface. <i>E-Journal of Surface Science and Nanotechnology</i> , 2019, 17, 56-60.	0.4	2
18	Relationship between electrical properties and interface structures of SiO ₂ /4H-SiC prepared by dry and wet oxidation. <i>AIP Advances</i> , 2019, 9, .	1.3	9

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19	Chemical-state-discriminated hard X-ray photoelectron diffraction study for polar InN. Journal of Surface Analysis (Online), 2019, 26, 138-139.	0.1	0
20	Surface and bulk electronic structures of unintentionally and Mg-doped In _{0.7} Ga _{0.3} N epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2018, 123, 095701.	2.5	1
21	Study of Sn and Mg doping effects on TiO ₂ /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2018, 57, 04FJ04.	1.5	0
22	Determination of the input parameters for inelastic background analysis combined with HAXPES using a reference sample. Applied Surface Science, 2018, 432, 60-70.	6.1	24
23	Forming mechanism of Te-based conductive-bridge memories. Applied Surface Science, 2018, 432, 34-40.	6.1	9
24	Near Surface Structures and the Electronic States of Polar InN. ECS Transactions, 2018, 86, 103-108.	0.5	0
25	Quantitative determination of elemental diffusion from deeply buried layers by photoelectron spectroscopy. Journal of Applied Physics, 2018, 124, .	2.5	22
26	1 year study in Grenoble. Vacuum and Surface Science, 2018, 61, 813-814.	0.1	0
27	Formation of a In ⁺ Se Surface Species by NaF/KF Postdeposition Treatment of Cu(In,Ga)Se ₂ Thin-Film Solar Cell Absorbers. ACS Applied Materials & Interfaces, 2017, 9, 3581-3589.	8.0	94
28	Hard X-Ray Photoelectron Spectroscopic Study on High-k Dielectrics Based Resistive Random Access Memory. ECS Transactions, 2017, 75, 39-47.	0.5	0
29	Surface and bulk electronic structures of heavily Mg-doped InN epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2017, 121, .	2.5	5
30	Photoelectron spectroscopic study of electronic state and surface structure of In ₂ O ₃ single crystals. Applied Physics Express, 2017, 10, 011102.	2.4	9
31	Effect of Y and Mn doping into rutile type TiO ₂ /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2017, 56, 06GF11.	1.5	3
32	Direct Observation of the Energy Distribution of Interface States at SiO ₂ /4H-SiC Interface: Operando Hard X-ray Photoelectron Spectroscopic Study. Hyomen Kagaku, 2017, 38, 347-350.	0.0	0
33	Thin-film growth of (110) rutile TiO ₂ on (100) Ge substrate by pulsed laser deposition. Japanese Journal of Applied Physics, 2016, 55, 06GG06.	1.5	2
34	Bottom-electrode effect on switching behavior and interface reaction in nanoionic-based resistive changing memory. Japanese Journal of Applied Physics, 2016, 55, 08PC03.	1.5	1
35	Characterization of 'metal resist' for EUV lithography. Proceedings of SPIE, 2016, , .	0.8	8
36	Direct Observation of Energy Distribution of Interface States at SiO ₂ /4H-SiC Interface. ECS Transactions, 2016, 75, 207-211.	0.5	0

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37	<i>In Situ</i> Tuning of Magnetization and Magnetoresistance in Fe ₃ O ₄ Thin Film Achieved with All-Solid-State Redox Device. ACS Nano, 2016, 10, 1655-1661.	14.6	80
38	Interface stability of electrode/Bi-containing relaxor ferroelectric oxide for high-temperature operational capacitor. Japanese Journal of Applied Physics, 2016, 55, 06GJ12.	1.5	1
39	Formation of Amorphous Pt Oxides: Characterization and Their Catalysis. Materials Transactions, 2015, 56, 490-494.	1.2	3
40	Electronic structure of the polymer-cathode interface of an organic electroluminescent device investigated using operando hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2015, 118, 085308.	2.5	1
41	Bias induced Cu ion migration behavior in resistive change memory structure observed by hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 06FG01.	1.5	3
42	Ge incorporated epitaxy of (110) rutile TiO ₂ on (100) Ge single crystal at low temperature by pulsed laser deposition. Thin Solid Films, 2015, 591, 105-110.	1.8	8
43	Hard x-ray photoelectron spectroscopy study of Ge ₂ Sb ₂ Te ₅ ; as-deposited amorphous, crystalline, and laser-reamorphized. Applied Physics Letters, 2014, 104, 061909.	3.3	7
44	Direct observation of bias-dependence potential distribution in metal/HfO ₂ gate stack structures by hard x-ray photoelectron spectroscopy under device operation. Journal of Applied Physics, 2014, 115, 043721.	2.5	3
45	Smart Decoration of Mesoporous TiO ₂ Nanospheres with Noble Metal Alloy Nanoparticles into Core-Shell, Yolk-Core-Shell, and Surface-Dispersion Morphologies. European Journal of Inorganic Chemistry, 2014, 2014, 4254-4257.	2.0	10
46	(Invited) Photoelectron Spectroscopic Study on High-k Dielectrics Based Nanoionics-Type ReRAM Structure under Bias Operation. ECS Transactions, 2014, 61, 301-310.	0.5	0
47	Bias dependent potential distribution of a Pt/HfO ₂ /SiO ₂ /Si gate structure obtained from a bias application in hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2014, 53, 05FH05.	1.5	1
48	NbPt ₃ Intermetallic Nanoparticles: Highly Stable and CO-tolerant Electrocatalyst for Fuel Oxidation. ChemElectroChem, 2014, 1, 728-732.	3.4	31
49	Photoelectron spectroscopic study on band alignment of poly(3-hexylthiophene-2,5-diyl)/polar-ZnO heterointerface. Thin Solid Films, 2014, 554, 194-198.	1.8	3
50	Identifying the Electronic Character and Role of the Mn States in the Valence Band of (Ga,Mn)As. Physical Review Letters, 2013, 111, 097201.	7.8	36
51	Direct observation of redox state modulation at carbon/amorphous tantalum oxide thin film hetero-interface probed by means of in situ hard X-ray photoemission spectroscopy. Solid State Ionics, 2013, 253, 110-118.	2.7	21
52	Chemical insight into electroforming of resistive switching manganite heterostructures. Nanoscale, 2013, 5, 3954.	5.6	44
53	Photoelectron spectroscopic study of band alignment of polymer/ZnO photovoltaic device structure. Applied Physics Letters, 2013, 102, .	3.3	24
54	Room temperature redox reaction by oxide ion migration at carbon/Gd-doped CeO ₂ heterointerface probed by an <i>in situ</i> hard x-ray photoemission and soft x-ray absorption spectroscopies. Science and Technology of Advanced Materials, 2013, 14, 045001.	6.1	21

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55	New Direct Spectroscopic Method for Determination of Bias-Dependent Electronic States: Hard X-ray Photoelectron Spectroscopy Under Device Operation. Japanese Journal of Applied Physics, 2013, 52, 108005.	1.5	4
56	Impact of Mg concentration on energy-band-depth profile of Mg-doped InN epilayers analyzed by hard X-ray photoelectron spectroscopy. Applied Physics Letters, 2013, 103, .	3.3	8
57	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	17
58	Investigation of the near-surface structures of polar InN films by chemical-state-discriminated hard X-ray photoelectron diffraction. Applied Physics Letters, 2013, 102, .	3.3	8
59	Bias-voltage application in a hard x-ray photoelectron spectroscopic study of the interface states at oxide/Si(100) interfaces. Journal of Applied Physics, 2013, 113, .	2.5	19
60	Investigation of the Effect of Oxygen on the Near-Surface Electron Accumulation in Nonpolar m-Plane (10 $\bar{1}$ l,0) InN Film by Hard X-ray Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2013, 52, 08JD01.	1.5	2
61	Wet Chemical Synthesis of Ni-Al Nanoparticles at Ambient Condition. Advanced Materials Research, 2012, 557-559, 442-447.	0.3	0
62	Strong Correlation Between Oxygen Donor and Near-Surface Electron Accumulation in Undoped and Mg-Doped In-Polar InN Films. Applied Physics Express, 2012, 5, 031002.	2.4	6
63	Polarity-dependent photoemission spectra of wurtzite-type zinc oxide. Applied Physics Letters, 2012, 100, .	3.3	32
64	Sulfur-mediated palladium catalyst immobilized on a GaAs surface. Journal of Applied Physics, 2012, 111, 124908.	2.5	3
65	Band bending and surface defects in In ²⁺ -Ga ₂ O ₃ . Applied Physics Letters, 2012, 100, .	3.3	82
66	Hard x-ray photoelectron spectroscopy study on band alignment at poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/ZnO interface. Applied Physics Letters, 2012, 101, .	3.3	21
67	Electronic structure of delta-doped La:SrTiO ₃ layers by hard x-ray photoelectron spectroscopy. Applied Physics Letters, 2012, 100, 261603.	3.3	25
68	Post-synthesis dispersion of metal nanoparticles by poly(amidoamine) dendrimers: size-selective inclusion, water solubilization, and improved catalytic performance. Chemical Communications, 2012, 48, 7441.	4.1	9
69	Hydroxylated surface of GaAs as a scaffold for a heterogeneous Pd catalyst. Physical Chemistry Chemical Physics, 2012, 14, 1424-1430.	2.8	6
70	Observation of filament formation process of Cu/HfO ₂ /Pt ReRAM structure by hard x-ray photoelectron spectroscopy under bias operation. Journal of Materials Research, 2012, 27, 869-878.	2.6	7
71	Bulk electronic structure of the dilute magnetic semiconductor Ga _{1-x} MnxAs through hard X-ray angle-resolved photoemission. Nature Materials, 2012, 11, 957-962.	27.5	117
72	Nondestructive characterization of a TiN metal gate: Chemical and structural properties by means of standing-wave hard x-ray photoemission spectroscopy. Journal of Applied Physics, 2012, 112, .	2.5	12

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73	Observation of boron diffusion in an annealed Ta/CoFeB/MgO magnetic tunnel junction with standing-wave hard x-ray photoemission. Applied Physics Letters, 2012, 101, .	3.3	64
74	Determination of Schottky barrier profile at Pt/SrTiO ₃ :Nb junction by x-ray photoemission. Applied Physics Letters, 2012, 101, .	3.3	27
75	Effect of near atmospheric pressure nitrogen plasma treatment on Pt/ZnO interface. Journal of Applied Physics, 2012, 112, .	2.5	2
76	Electronic Structure Changes across the Metamagnetic Transition in FeRh via Hard X-Ray Photoemission. Physical Review Letters, 2012, 108, 257208.	7.8	68
77	Real-space observation of local anisotropic correlation between buckled dimers on Si(100) induced by a bidentate adsorbed molecule. Chemical Communications, 2011, 47, 10392.	4.1	4
78	Electronic and crystallographic structure, hard x-ray photoemission, and mechanical and transport properties of the half-metallic Heusler compound Co ₂ MnGe. Physical Review B, 2011, 84, .	3.2	56
79	XPS study of Sb-/In-doping and surface pinning effects on the Fermi level in SnO ₂ (101) thin films. Applied Physics Letters, 2011, 98, .	3.3	38
80	Depletion of the In ₂ O ₃ (001) and (111) surface electron accumulation by an oxygen plasma surface treatment. Applied Physics Letters, 2011, 98, .	3.3	71
81	Probing bulk electronic structure with hard X-ray angle-resolved photoemission. Nature Materials, 2011, 10, 759-764.	27.5	153
82	Electronic, structural, and magnetic properties of the half-metallic ferromagnetic quaternary Heusler compounds CoFeMnZ ₂ (Z = Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn, Ga, In, Sn, Pb, Bi, Po, At, Rn). Physical Review B, 2011, 84, .	3.2	221
83	Energy-level alignments and photo-induced carrier processes at the heteromolecular interface of quaternary and N,N'-dicyclohexyl-3,4,9,10-perylene-dicarboximide. Physical Chemistry Chemical Physics, 2011, 13, 6280.	2.8	25
84	Structural analysis and electrical properties of pure Ge ₃ N ₄ dielectric layers formed by an atmospheric-pressure nitrogen plasma. Journal of Applied Physics, 2011, 110, 064103.	2.5	9
85	Role of residual transition-metal atoms in oxygen reduction reaction in cobalt phthalocyanine-based carbon cathode catalysts for polymer electrolyte fuel cell. Journal of Power Sources, 2011, 196, 8346-8351.	7.8	38
86	X-ray photoemission spectroscopy analysis of N-containing carbon-based cathode catalysts for polymer electrolyte fuel cells. Journal of Power Sources, 2011, 196, 1006-1011.	7.8	98
87	Activity of oxygen reduction reaction on small amount of amorphous CeO promoted Pt cathode for fuel cell application. Electrochimica Acta, 2011, 56, 3874-3883.	5.2	75
88	X-dependent electronic structure of YbXCu ₄ (X=Cd, In, Sn) investigated by hard X-ray photoemission spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2011, 184, 203-206.	1.7	7
89	Temperature-Induced Valence Transition of EuPd ₂ Si ₂ Studied by Hard X-ray Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2011, 50, 05FD03.	1.5	7
90	Conduction-band electronic states of YbInCu ₄ studied by photoemission and soft x-ray absorption spectroscopies. Physical Review B, 2011, 84, .	3.2	11

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91	Identification of Different Electron Screening Behavior Between the Bulk and Surface of (Ga,Mn)As. Physical Review Letters, 2011, 107, 187203.	7.8	24
92	Insulating state of ultrathin epitaxial LaNiO ₃ thin films detected by hard x-ray photoemission. Physical Review B, 2011, 84, .	3.2	35
93	Bias application hard x-ray photoelectron spectroscopy study of forming process of Cu/HfO ₂ /Pt resistive random access memory structure. Applied Physics Letters, 2011, 99, .	3.3	56
94	Hard x-ray photoemission study of near-Heusler Fe ₂ Si alloys. Physical Review B, 2011, 83, .	3.2	13
95	Delta-doped epitaxial La:SrTiO ₃ field-effect transistor. Applied Physics Letters, 2011, 98, 242113.	3.3	6
96	Defects in ZnO transparent conductors studied by capacitance transients at ZnO/Si interface. Applied Physics Letters, 2011, 98, 082101.	3.3	18
97	(Invited) Direct Observation of Electronic States in Gate Stack Structures: XPS under Device Operation. ECS Transactions, 2011, 41, 331-336.	0.5	4
98	Direct Observation of Electronic States in Gate Stack Structures: XPS under Device Operation. ECS Meeting Abstracts, 2011, .	0.0	0
99	Hard x-ray photoemission spectroscopic investigation of palladium catalysts immobilized on a GaAs(001) surface. Journal of Applied Physics, 2010, 108, .	2.5	9
100	Present Status of the NIMS Contract Beamline BL15XU at SPring-8. AIP Conference Proceedings, 2010, .	0.4	127
101	Sulfur Modification of Au via Treatment with Piranha Solution Provides Low-Pd Releasing and Recyclable Pd Material, SAPd. Journal of the American Chemical Society, 2010, 132, 7270-7272.	13.7	77
102	Pt and Sn Doped Sputtered CeO ₂ Electrodes for Fuel Cell Applications. Fuel Cells, 2010, 10, 139-144.	2.4	14
103	Bias-voltage Application in Hard X-Ray Photoelectron Spectroscopy for Characterization of Advanced Materials. E-Journal of Surface Science and Nanotechnology, 2010, 8, 81-83.	0.4	15
104	Thermoelectric properties and electronic structure of substituted Heusler compounds: NiTiO.3 α xScxZr0.35Hf0.35Sn. Applied Physics Letters, 2010, 97, .	3.3	22
105	Schottky barrier height behavior of PtRu alloy contacts on single-crystal n-ZnO. Journal of Applied Physics, 2010, 107, .	2.5	6
106	Oxygen migration at Pt/HfO ₂ /Pt interface under bias operation. Applied Physics Letters, 2010, 97, .	3.3	59
107	Interface properties of magnetic tunnel junction $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_2/\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_2/\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_2$. Physical Review B, 2010, 82, .	3.2	71
108	Characterization of Surface Structure Evolution in Ni ₃ Al Foil Catalysts by Hard X-ray Photoelectron Spectroscopy. Journal of Physical Chemistry C, 2010, 114, 6047-6053.	3.1	22

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109	Interface structure and the chemical states of Pt film on polar-ZnO single crystal. Applied Physics Letters, 2009, 94, 221904.	3.3	18
110	ELECTRONIC STRUCTURES OF NAKED AND MOLECULAR ENCAPSULATED Au NANOPARTICLES. International Journal of Nanoscience, 2009, 08, 181-184.	0.7	0
111	Low-Temperature Surface Photochemistry of π -bonded Ethylene on Si(100)(4 \times 4 $\sqrt{2}$). Japanese Journal of Applied Physics, 2009, 48, 08JB14.	1.5	2
112	Electron Transport Properties and Dielectric Breakdown of Alkyl Monolayers Chemisorbed on a Highly Doped n-Type Si(111) Surface. Japanese Journal of Applied Physics, 2009, 48, 055003.	1.5	9
113	The growth process of first water layer and crystalline ice on the Rh(111) surface. Journal of Chemical Physics, 2009, 130, 034706.	3.0	25
114	Au ⁺ and Au ³⁺ ions in CeO ₂ -rf-sputtered thin films. Journal Physics D: Applied Physics, 2009, 42, 115301.	2.8	32
115	Development of a Recyclable and Low-Leaching Palladium Catalyst Supported on Sulfur-Modified Gallium Arsenide(001) for Use in Suzuki-Miyaura Coupling. ChemCatChem, 2009, 1, 279-285.	3.7	24
116	Degradation of interface integrity between a high-k dielectric thin film and a gate electrode due to excess oxygen in the film. , 2009, , .		1
117	Hard x-ray photoelectron spectroscopy of buried Heusler compounds. Journal Physics D: Applied Physics, 2009, 42, 084010.	2.8	18
118	Analysis of ITO/Mg:GaN interfaces by synchrotron radiation hard X-ray photoemission spectroscopy and their electrical characteristics. Applied Surface Science, 2008, 255, 2149-2152.	6.1	3
119	Coverage-dependent sticking probability and desorption kinetics of water molecules on Rh(111). Journal of Chemical Physics, 2008, 129, 016101.	3.0	10
120	Formation of Ni ₃ C Nanocrystals by Thermolysis of Nickel Acetylacetonate in Oleylamine: Characterization Using Hard X-ray Photoelectron Spectroscopy. Chemistry of Materials, 2008, 20, 4156-4160.	6.7	162
121	Detection of the valence band in buried Co ₂ MnSi/MgO tunnel junctions by means of photoemission spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	46
122	Degradation of reliability of high-k gate dielectrics caused by point defects and residual stress. , 2008, , .		2
123	Low-Temperature STM and UPS Study of Adsorption States of 1,4-Cyclohexadiene on Si(100)(4 \times 4 $\sqrt{2}$). Journal of Physical Chemistry C, 2008, 112, 15009-15014.	3.1	2
124	Microscopic diffusion processes of NO on the Pt(997) surface. Journal of Chemical Physics, 2008, 128, 054701.	3.0	6
125	Determination of Band Structures of InN/GaN Interfaces by Synchrotron Radiation Hard X-ray Photoemission Spectroscopy. E-Journal of Surface Science and Nanotechnology, 2008, 6, 254-257.	0.4	1
126	Direct Observation of Valence and Conduction States near the SiO ₂ /Si(100) Interface. E-Journal of Surface Science and Nanotechnology, 2008, 6, 209-212.	0.4	2

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127	CYCLOADDITION REACTION BETWEEN ORGANIC MOLECULES AND Si(100) AND ELECTRONIC PROPERTIES OF ADSORBED MOLECULES. <i>International Journal of Nanoscience</i> , 2007, 06, 95-102.	0.7	1
128	Transient diffusion and cluster formation of water molecules on Rh(111) at 20K. <i>Journal of Chemical Physics</i> , 2007, 126, 141102.	3.0	9
129	Soft X-Ray Absorption and Emission Study of Silicon Oxynitride/Si(100) Interface. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L77-L79.	1.5	5
130	Regioselective Cycloaddition Reaction of Alkene Molecules with the Asymmetric Dimer on Si(100)c(4Å-2). <i>Journal of the American Chemical Society</i> , 2007, 129, 1242-1245.	13.7	7
131	Adsorption States and Dissociation Processes of Oxygen Molecules on Cu(100) at Low Temperature. <i>Journal of Physical Chemistry C</i> , 2007, 111, 15059-15063.	3.1	11
132	Fabrication and analysis of buried iron silicide microstructures using a focused low energy electron beam. <i>Surface Science</i> , 2007, 601, 5108-5111.	1.9	6
133	Compact UHV system for fabrication and in situ analysis of electron beam deposited structures using a focused low energy electron beam. <i>Review of Scientific Instruments</i> , 2006, 77, 053702.	1.3	8
134	The first layer of water on Rh(111): Microscopic structure and desorption kinetics. <i>Journal of Chemical Physics</i> , 2006, 125, 054717.	3.0	33
135	Effects of interface roughness on the local valence electronic structure at the SiO ₂ /Si interface: Soft X-ray absorption and emission study. <i>European Physical Journal Special Topics</i> , 2006, 132, 259-262.	0.2	2
136	Direct observation of the site-specific valence electronic structure at SiO ₂ /Si(111) interface. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006, 4, 280-284.	0.4	2
137	Method of observation of low density interface states by means of X-ray photoelectron spectroscopy under bias and passivation by cyanide ions. <i>Applied Surface Science</i> , 2006, 252, 7700-7712.	6.1	18
138	Methods of observation and elimination of semiconductor defect states. <i>Solar Energy</i> , 2006, 80, 645-652.	6.1	26
139	Search for adsorption potential energy minima of NO on Pt(997) at 11K. <i>Surface Science</i> , 2006, 600, 3560-3563.	1.9	8
140	Heat Transport Analysis of Femtosecond Laser Ablation with Full Lagrangian Modified Molecular Dynamics. <i>International Journal of Thermophysics</i> , 2006, 27, 627-646.	2.1	6
141	Adsorption states of NO on the Pt(111) step surface. <i>Surface Science</i> , 2006, 600, 3477-3483.	1.9	22
142	Direct observation of site-specific valence electronic structure at the SiO ₂ /Si interface. <i>Physical Review B</i> , 2006, 73, .	3.2	31
143	Water Adsorption on Rh(111) at 20 K: From Monomer to Bulk Amorphous Ice. <i>Journal of Physical Chemistry B</i> , 2005, 109, 5816-5823.	2.6	38
144	Precursor Mediated Cycloaddition Reaction of Ethylene on Si(100)c(4*2). <i>Hyomen Kagaku</i> , 2005, 26, 474-479.	0.0	0

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145	Site-specific Observation of the Valence Electronic Structure at SiO ₂ /Si Interface by Means of Soft X-ray Absorption and Emission Spectroscopy. <i>Hyomen Kagaku</i> , 2005, 26, 514-517.	0.0	1
146	Residual gas effects on high-resolution Si2p spectra of Si(100)c(4Å–2). <i>Surface Science</i> , 2004, 566-568, 467-470.	1.9	6
147	Ground state of the Si(001) surface revisited?is seeing believing?. <i>Progress in Surface Science</i> , 2004, 76, 147-162.	8.3	47
148	Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface. <i>Applied Surface Science</i> , 2004, 234, 162-167.	6.1	12
149	Selective functionalization of the Si(100) surface by switching the adsorption linkage of a bifunctional organic molecule. <i>Chemical Physics Letters</i> , 2004, 388, 27-30.	2.6	14
150	Low-energy electron-stimulated chemical reactions of CO in water ice. <i>Chemical Physics Letters</i> , 2004, 388, 384-388.	2.6	14
151	Precursor Mediated Cycloaddition Reaction of Ethylene to the Si(100)c(4 Å– 2) Surface. <i>Journal of the American Chemical Society</i> , 2004, 126, 9922-9923.	13.7	55
152	The Precursor Mediated Chemisorption of Vinyl Bromide on Si(100)c(4Å–2). <i>Journal of Physical Chemistry B</i> , 2004, 108, 5703-5708.	2.6	22
153	Highly Selective Surface Lewis Acid–Base Reaction: Trimethylamine on Si(100)c(4Å–2). <i>Journal of Physical Chemistry B</i> , 2004, 108, 4737-4742.	2.6	26
154	Vibrational structure in C 1s photoelectron spectra of ethylene on the Si(100)(2Å–1) surface. <i>Chemical Physics Letters</i> , 2003, 374, 476-481.	2.6	9
155	Electronic states and chemical reactivity of Si(100)c(4Å–2) surface at low temperature studied by high resolution Si 2p core level photoelectron spectroscopy. <i>Surface Science</i> , 2003, 532-535, 716-720.	1.9	3
156	Adsorbed states of 1,1,1-trifluoro-2-propanol on Si(100). <i>Surface Science</i> , 2003, 529, 288-294.	1.9	2
157	Intermolecular interaction and arrangements of adsorbed 1,4-cyclohexadiene molecules on Si()(2Å–1). <i>Surface Science</i> , 2003, 531, 199-207.	1.9	13
158	Purely Site-Specific Chemisorption and Conformation of Trimethylamine on Si(100)c(4 Å– 2). <i>Journal of the American Chemical Society</i> , 2003, 125, 9252-9253.	13.7	24
159	Microscopic observation of precursor-mediated adsorption process of NH ₃ on Si(100)c(4Å–2) using STM. <i>Physical Review B</i> , 2003, 68, .	3.2	41
160	Model for C defect on Si(100): The dissociative adsorption of a single water molecule on two adjacent dimers. <i>Physical Review B</i> , 2003, 67, .	3.2	77
161	Microscopic adsorption process of CO on Si(100)c(4Å–2) by means of low-temperature scanning tunneling microscopy. <i>Physical Review B</i> , 2003, 68, .	3.2	15
162	Lateral Displacement by Transient Mobility in Chemisorption of CO on Pt(997). <i>Physical Review Letters</i> , 2003, 90, 248301.	7.8	43

#	ARTICLE	IF	CITATIONS
163	Vibrational Structure of Adsorbates As Revealed by High Resolution Core Level Photoelectron Spectra. Hyomen Kagaku, 2003, 24, 301-305.	0.0	0
164	Direct Evidence for Asymmetric Dimer on Si(100) at Low Temperature by Means of High-Resolution Si 2p Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2002, 41, L272-L274.	1.5	20
165	Electronic and Vibrational States of Cyclopentene on Si(100)(2Å-1). Journal of Physical Chemistry B, 2002, 106, 1691-1696.	2.6	21
166	Chemical nature of nanostructures of La _{0.6} Sr _{0.4} MnO ₃ on SrTiO ₃ (100). Surface Science, 2002, 514, 54-59.	1.9	40
167	Nature of interface bonding of ethylene and benzene with Si(100)c(4Å-2): angle-dependent Si2p high resolution photoelectron spectroscopy studies. Surface Science, 2002, 513, 413-421.	1.9	21
168	Bonding and Structure of 1,4-Cyclohexadiene Chemisorbed on Si(100)(2Å-1). Journal of Physical Chemistry B, 2001, 105, 3718-3723.	2.6	40
169	High resolution Si 2p photoelectron spectroscopy of unsaturated hydrocarbon molecules adsorbed on Si(100)c(4Å-2): the interface bonding and charge transfer between the molecule and the Si substrate. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 389-393.	1.7	20
170	Reaction mechanism and adsorbed states of cyclohexene on Si(100)(2Å-1). Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 383-387.	1.7	18
171	Adsorbed states of cyclopentene, cyclohexene, and 1,4-cyclohexadiene on Si(1 0 0)(2Å-1): towards the fabrication of novel organic films/Si hybrid structures. Applied Surface Science, 2001, 169-170, 172-175.	6.1	19
172	Adsorption state of 1,4-cyclohexadiene on Si(100)(2Å-1). Physical Review B, 2000, 62, 7576-7580.	3.2	39
173	Dependence of interface states in the Si band gap on oxide atomic density and interfacial roughness. Physical Review B, 1999, 59, 15872-15881.	3.2	43
174	Studies on interface states at ultrathin SiO ₂ /Si(100) interfaces by means of x-ray photoelectron spectroscopy under biases and their passivation by cyanide treatment. Journal of Applied Physics, 1998, 83, 2098-2103.	2.5	57
175	A new method for the growth of silicon oxide layers below 300Å°C by use of catalytic activity of platinum overlayers. Applied Surface Science, 1997, 108, 433-438.	6.1	12
176	Effects of interface roughness on the density of interface states at ultrathin oxide/Si interfaces: XPS measurements under biases. Applied Surface Science, 1997, 117-118, 176-180.	6.1	7
177	Interface states in the Si band-gap obtained from XPS measurements under biases. Surface Science, 1996, 357-358, 455-458.	1.9	5
178	Spectroscopic observation of interface states of ultrathin silicon oxide. Journal of Applied Physics, 1996, 79, 7051-7057.	2.5	56
179	Interface states at ultrathin oxide/Si(111) interfaces obtained from x-ray photoelectron spectroscopy measurements under biases. Applied Physics Letters, 1996, 69, 2276-2278.	3.3	33
180	Interface state-induced shift of the oxide and semiconductor core levels for metal-oxide-semiconductor devices. Journal of Applied Physics, 1996, 80, 1578-1582.	2.5	15

#	ARTICLE	IF	CITATIONS
181	Interface States for Si-Based MOS Devices with an Ultrathin Oxide Layer: X-Ray Photoelectron Spectroscopic Measurements under Biases. Japanese Journal of Applied Physics, 1995, 34, 959-964.	1.5	25
182	Energy distribution of surface states in the Si band-gap for MOS diodes obtained from XPS measurements under biases. Surface Science, 1995, 326, 124-132.	1.9	25
183	Direct Spectroscopic Evidence of Bias-Induced Shifts of Semiconductor Band Edges for Metal-Insulator-Semiconductor Diodes. Japanese Journal of Applied Physics, 1994, 33, L754-L756.	1.5	10
184	Multi-stage Decoding For Multi-level Block Modulation Codes And Its Performance Analysis. , 0, , .		2
185	New direct spectroscopic method for determination of the energy distribution of interface states. , 0, , .		0